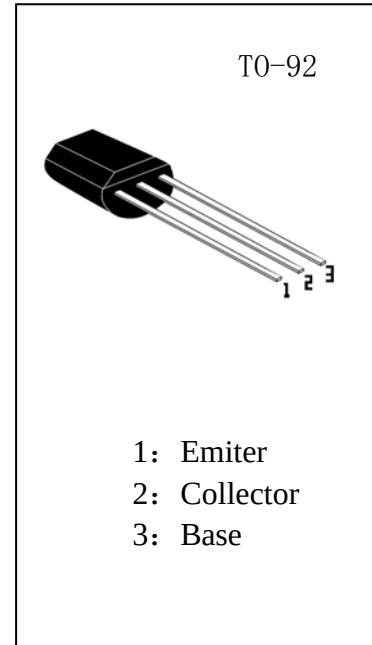


LOW FREQUENCY TRANSISTOR

- $I_c=150\text{mA}$, $I_b=50\text{mA}$
- $V_{cbo}=60\text{V}$
- 与 2SA1015 对管

极限参数(Absolute Maximum Ratings) $T_a=25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	60	V
Collector-Emitter Voltage	V_{ceo}	50	V
Emitter-Base Voltage	V_{ebo}	5	V
Collector Current	I_c	150	mA
Base current	I_b	50	mA
Collector Dissipation	P_c	400	m W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$


电性能(Electrical Characteristic) $T_a=25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=100\mu\text{A}$ $I_e=0$	60			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=1\text{mA}$ $I_b=0$	50			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=100\mu\text{A}$ $I_c=0$	5			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=60\text{V}$, $I_e=0$			100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=5\text{V}$, $I_c=0$			100	nA
I_{ceo}	Collector Cutoff Current	$V_{ce}=50\text{V}$, $I_b=0$			10	μA
$V_{ce(sat)}$	Collector-Emitter Saturation Voltage	$I_c=100\text{mA}$, $I_b=10\text{mA}$			0.25	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c=100\text{mA}$, $I_b=10\text{mA}$			1.0	V
H_{fe1}	DC Current Gain	$V_{ce}=6\text{V}$, $I_c=150\text{mA}$	25			
H_{fe2}	DC Current Gain	$V_{ce}=6\text{V}$, $I_c=2\text{mA}$	70		800	
C_{ob}	Output Capacitance	$V_{cb}=10\text{V}$, $I_e=0$, $f=1\text{MHz}$			3.5	PF
f_T	Current Gain-Bandwidth product	$V_{ce}=10\text{V}$, $I_c=1\text{mA}$,	80			MHz
NF	Noise Figure	$I_c=100\mu\text{A}$, $V_{ce}=6\text{V}$ $f=1\text{kHz}$, $R_g=10\text{k}\Omega$			10	dB

CLASS	O	Y	GR			BL		
Hfe2	70-140	120-240	200-240	240-350	350-400	350-450	450-600	600-700

